

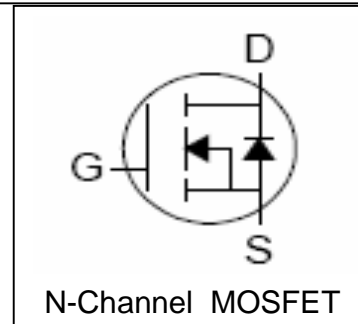
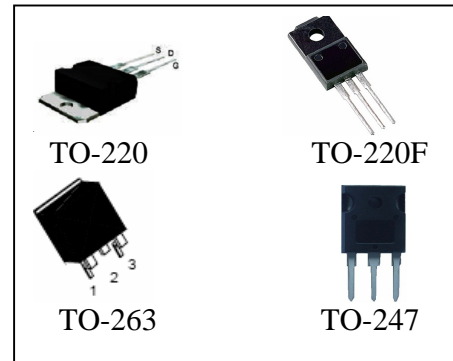
Features

- 100V/190A,
 $R_{DS(ON)} = 5m\Omega$ (Type) @ $V_{GS}=10V, I_{DS}=80A$
- Ultra Low On-Resistance
- Exceptional dv/dt capability
- Fast Switching and Fully Avalanche Rated
- 100% avalanche tested
- 175°C Operating Temperature
- Lead Free and Green Available

Applications

- Switching Application Systems

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 190	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 720 ^①	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 190 ^②	A
		$T_C=100^\circ\text{C}$ 120 ^②	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 250	W
		$T_C=100^\circ\text{C}$ 125	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.55	$^\circ\text{C/W}$
Drain-Source Avalanche Ratings			
E_{AS} ^③	Avalanche Energy, Single Pulsed	1240	mJ

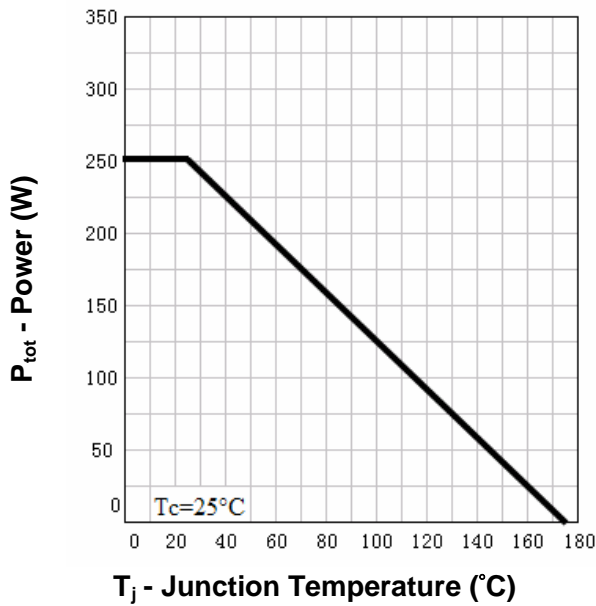
Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU1H190R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	100			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			1	μA
					30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=80A$		5	6.5	m Ω
Diode Characteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=80A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=80A, di_{SD}/dt=100A/\mu s$		89		ns
Q_{rr}	Reverse Recovery Charge			175		nC
Dynamic Characteristics ⁽⁵⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.2		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		6500		pF
C_{oss}	Output Capacitance			940		
C_{riss}	Reverse Transfer Capacitance			650		
$t_{d(ON)}$	Turn-on Delay Time			29		
t_r	Turn-on Rise Time	$V_{DD}=30V, R_L=30\Omega,$ $I_{DS}=80A, V_{GEN}=10V,$ $R_G=6\Omega$		38		
$t_{d(OFF)}$	Turn-off Delay Time			80		
t_f	Turn-off Fall Time			125		
Gate Charge Characteristics ⁽⁵⁾						
Q_g	Total Gate Charge	$V_{DS}=80V, V_{GS}=10V,$ $I_{DS}=80A$		158	208	nC
Q_{gs}	Gate-Source Charge			35		
Q_{gd}	Gate-Drain Charge			52		

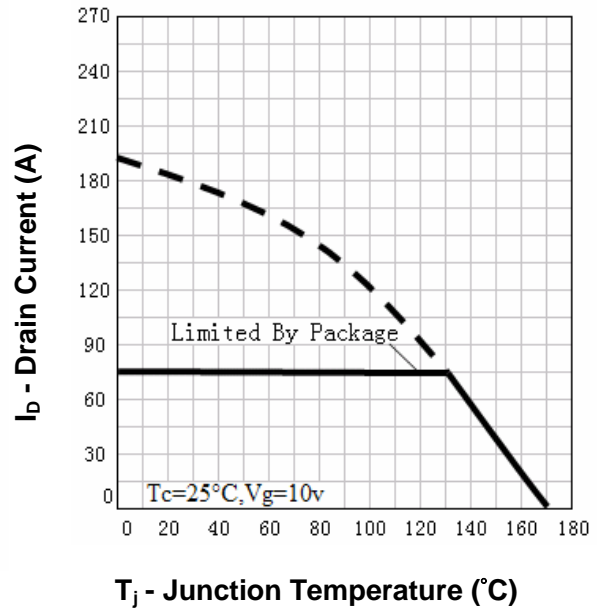
- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A..
 - ③ Limited by $T_{Jmax}, I_{AS}=65A, V_{DD}=48V, R_G=47\Omega$, Starting $T_J=25^\circ\text{C}$.
 - ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑤ Guaranteed by design, not subject to production testing.

Typical Characteristics

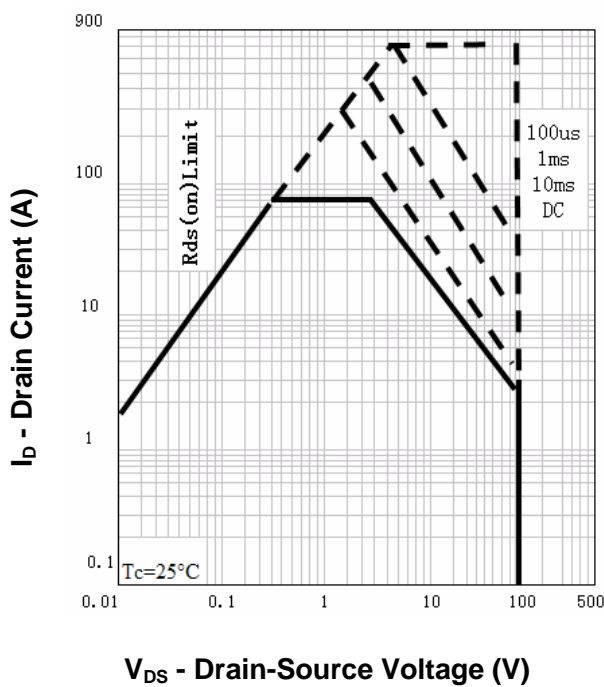
Power Dissipation



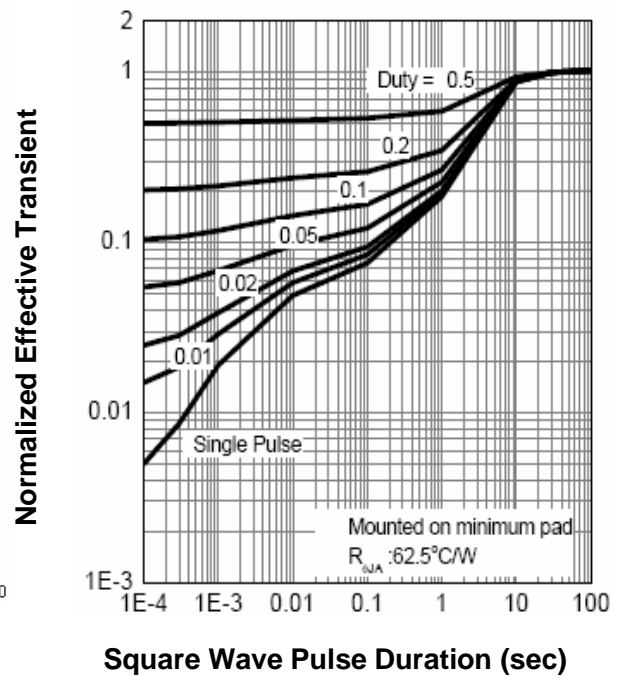
Drain Current



Safe Operation Area

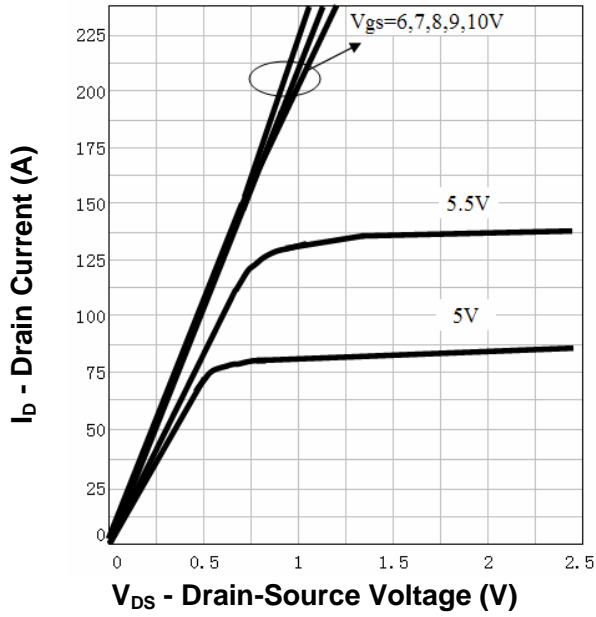


Thermal Transient Impedance

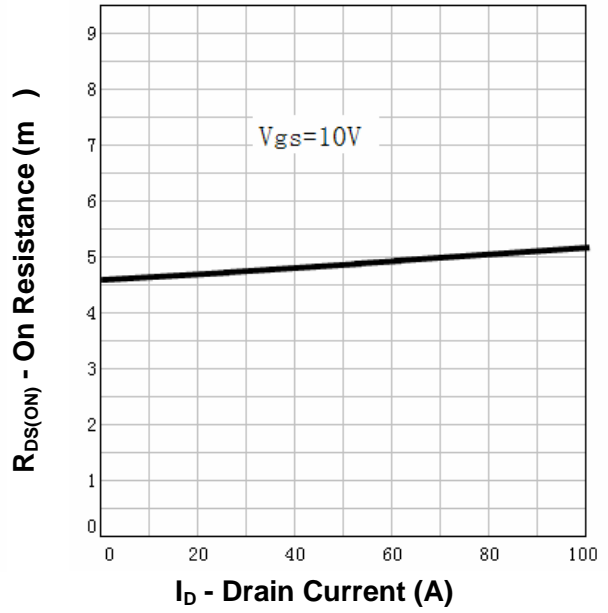


Typical Characteristics

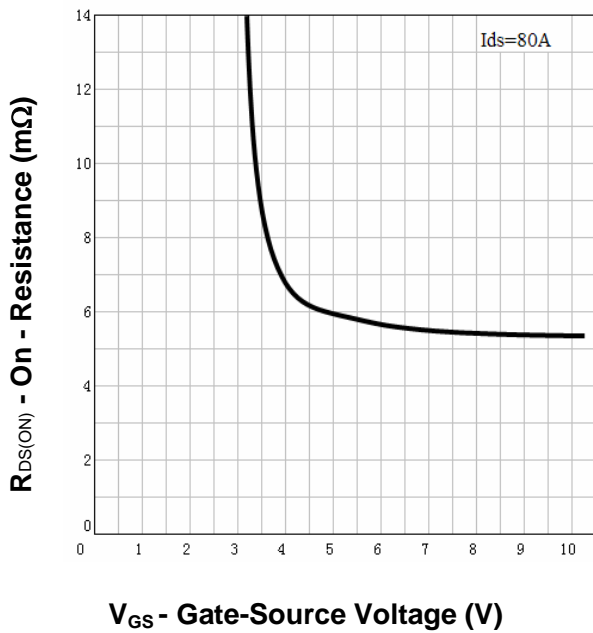
Output Characteristics



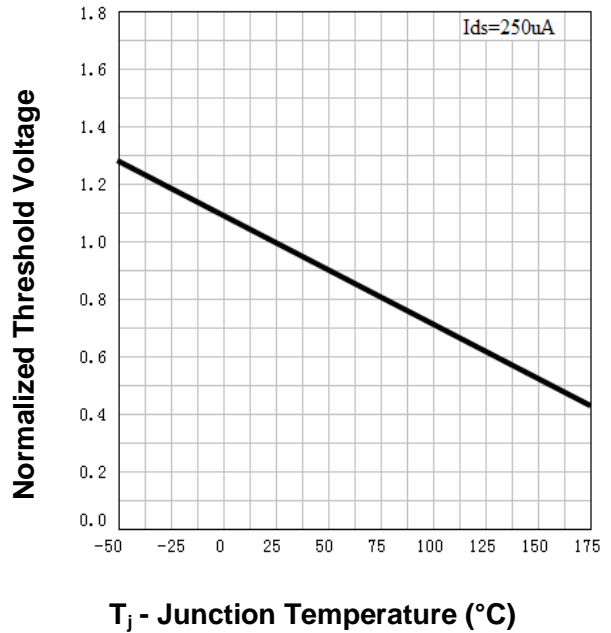
Drain-Source On Resistance



Drain-Source On Resistance

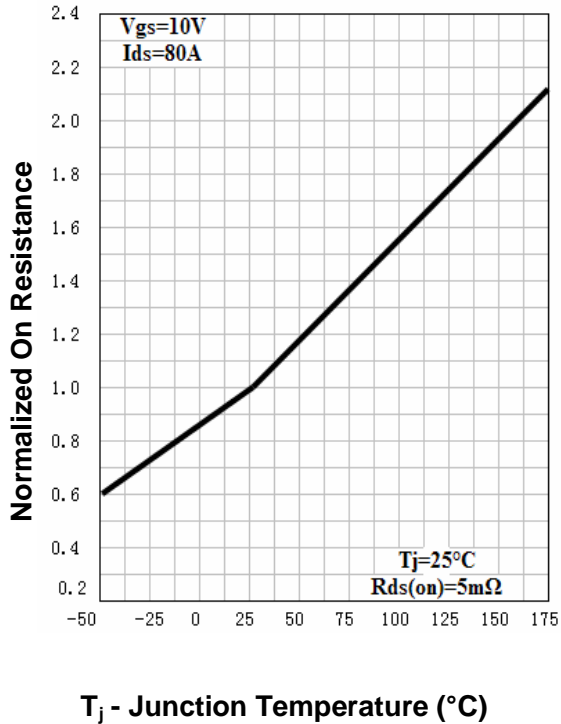


Gate Threshold Voltage

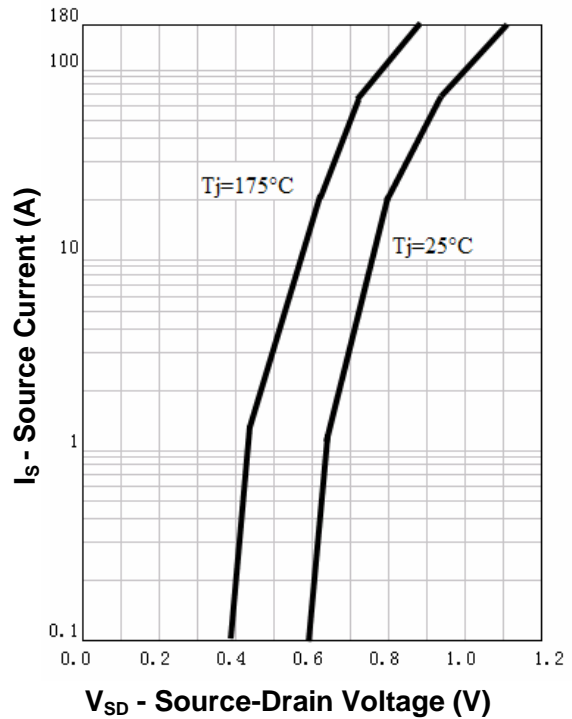


Typical Characteristics

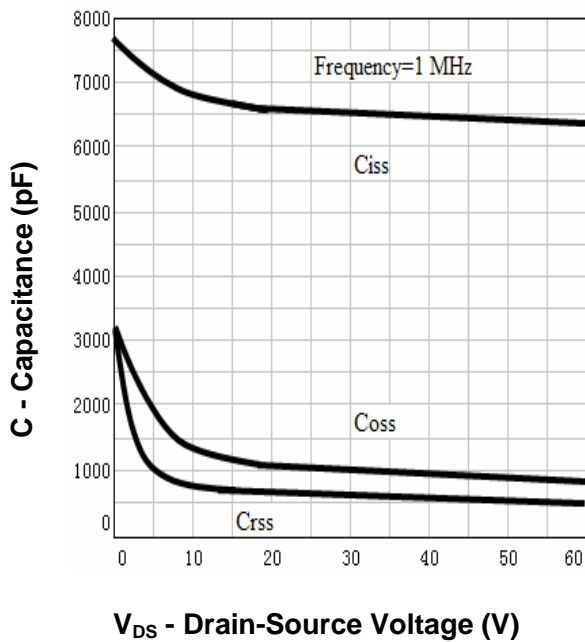
Drain-Source On Resistance



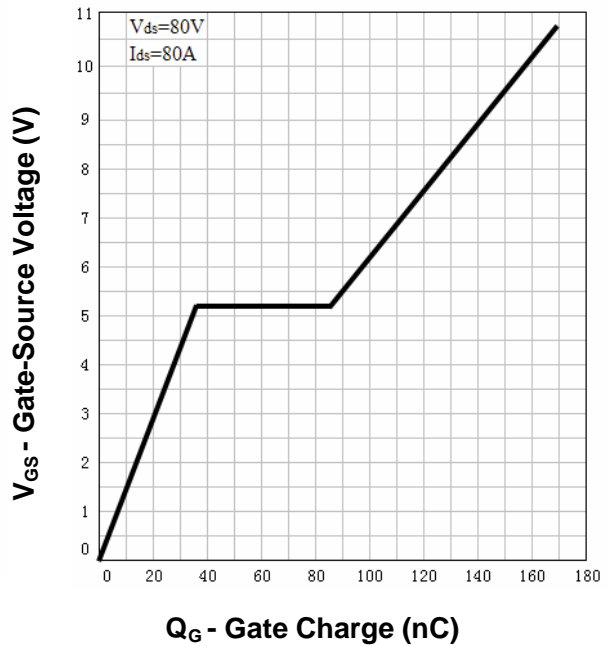
Source-Drain Diode Forward



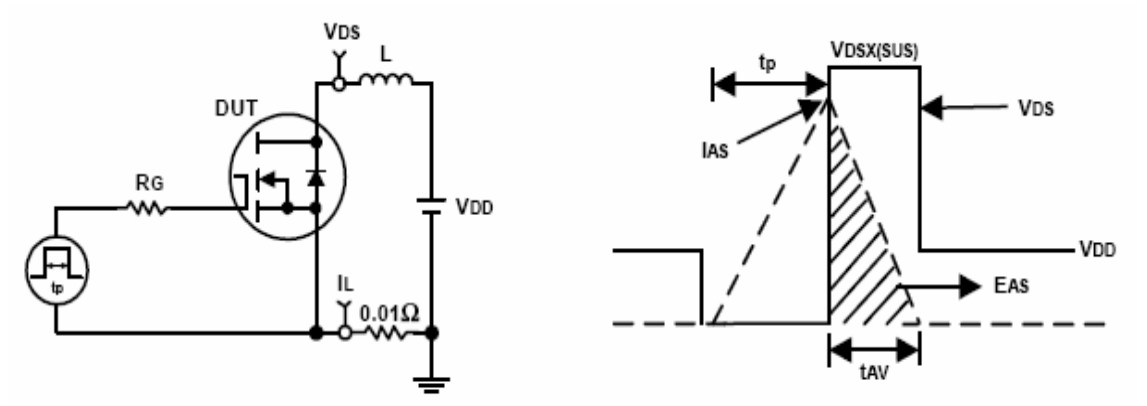
Capacitance



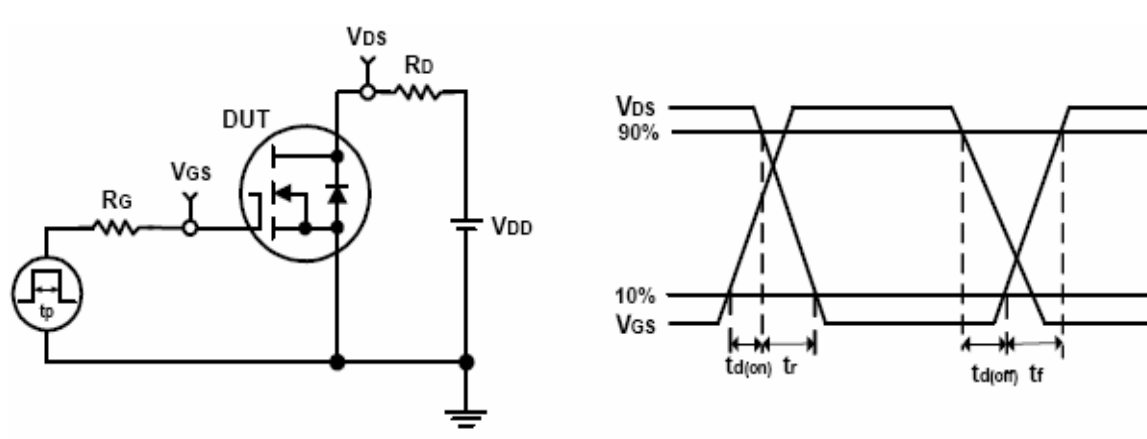
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Ordering and Marking Information**RU1H190****Package (Available)**

R : TO-220; S: TO-263 ; P: TO-220F

Operating Temperature Range

C : -55 to 175 °C

Assembly Material

G : Green & Lead Free

Packaging

T : TUBE

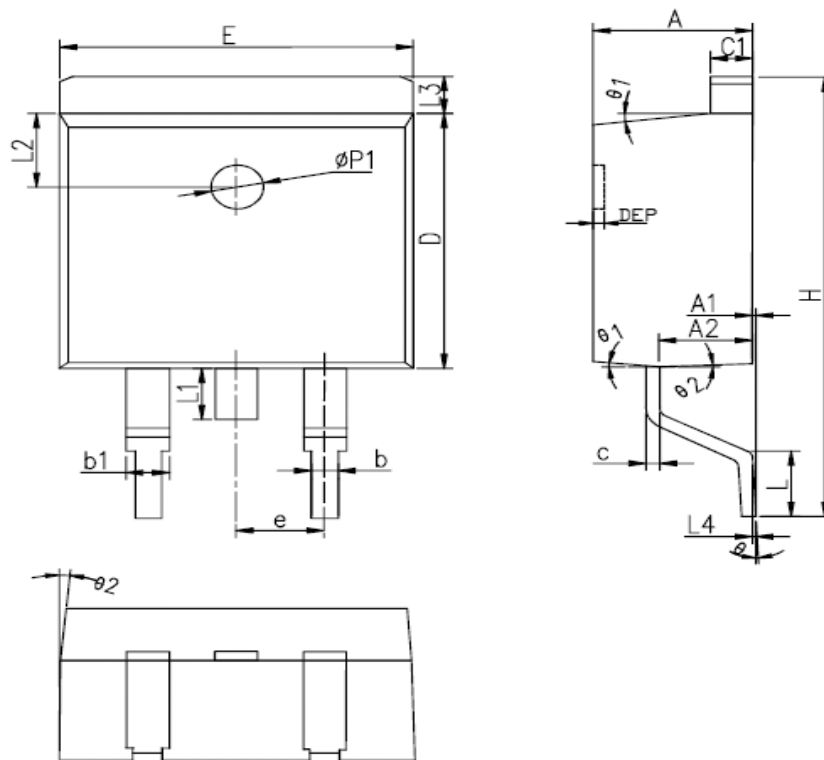
TR : Tape & Reel

Package Information
TO-220FB-3L


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	ϕ_{p1}	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC			0.1BSC		
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC			0.2BSC		
b	0.77	-	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
C	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	ϕ_p	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
E	9.70	9.90	10.10	0.382	0.389	0.398	θ_1	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	θ_2	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

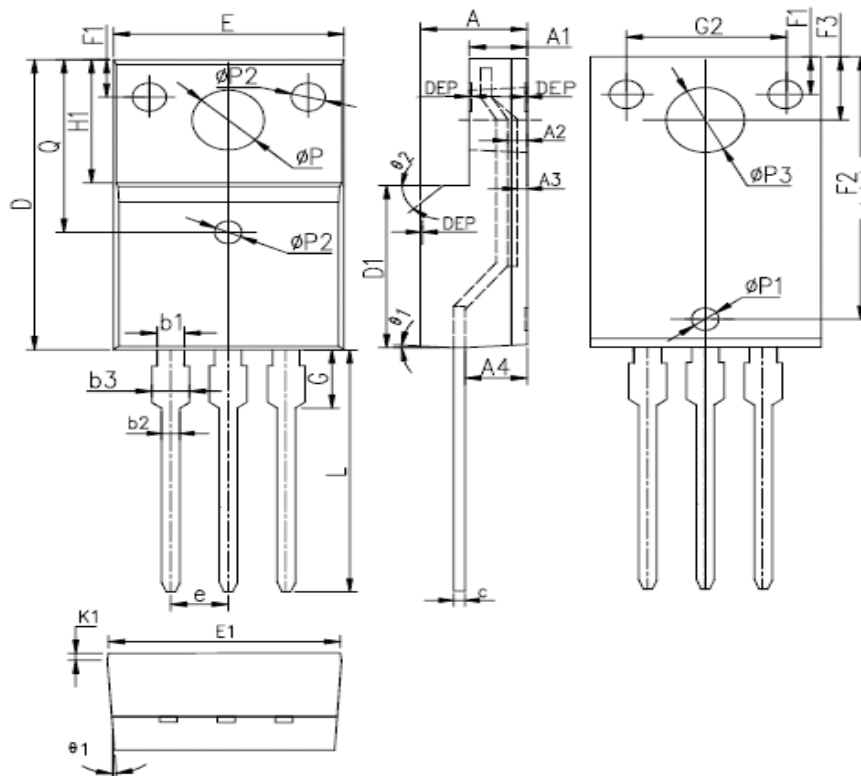
TO-263-2L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	L	2.00	2.30	2.60	0.079	0.090	0.102
A1	0	0.10	0.25	0	0.004	0.010	L3	1.17	1.27	1.40	0.046	0.050	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	-	-	1.70	-	-	0.067
b	0.77	-	0.90	0.030	-	0.035	L4	0.25BSC			0.01BSC		
b1	1.23	-	1.36	0.048	-	0.052	L2	2.50REF.			0.098REF.		
c	0.34	-	0.47	0.013	-	0.019	θ	0°	-	8°	0°	-	8°
C1	1.22	-	1.32	0.048	-	0.052	θ 1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.338	0.343	0.346	θ 2	1°	3°	5°	1°	3°	5°
E	10.00	10.16	10.26	0.394	0.4	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e	2.54BSC			0.1BSC			Øp1	1.40	1.50	1.60	0.055	0.059	0.063
H	14.70	15.10	15.50	0.579	0.594	0.610							

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TO-220F-3L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
E	9.96	10.16	10.36	0.392	0.400	0.408	$\phi p3$	-	3.450	-	-	0.136	-
A	4.50	4.70	4.90	0.177	0.185	0.193	$\theta 1$	5°	7°	9°	5°	7°	9°
A1	2.34	2.54	2.74	0.092	0.100	0.108	$\theta 2$	-	45°	-	-	45°	-
A2	0.95	1.05	1.15	0.037	0.041	0.045	DEP	0.05	0.10	0.15	0.002	0.004	0.006
A3	0.42	0.52	0.62	0.017	0.020	0.024	F1	1.90	2.00	2.10	0.075	0.079	0.083
A4	2.65	2.75	2.85	0.104	0.108	0.112	F2	13.61	13.81	14.01	0.536	0.544	0.552
c	-	0.50	-	-	0.020	-	F3	3.20	3.30	3.40	0.126	0.130	0.134
D	15.67	15.87	16.07	0.617	0.625	0.633	G	3.25	3.45	3.65	0.128	0.136	0.144
Q	8.80	9.00	9.20	0.346	0.354	0.362	G1	5.90	6.00	6.10	0.232	0.236	0.240
H1	6.48	6.68	6.88	0.255	0.263	0.271	G2	6.90	7.00	7.10	0.272	0.276	0.280
e	2.54BSC			0.1BSC			b1	1.17	1.20	1.24	0.046	0.047	0.048
ϕp	-	3.183	-	-	0.125	-	b2	0.77	0.8	0.85	0.030	0.031	0.033
L	12.78	12.98	13.18	0.503	0.511	0.519	b3	1.10	1.30	1.50	0.043	0.051	0.059
D1	8.99	9.19	9.39	0.354	0.362	0.370	E1	9.8	10.00	10.20	0.386	0.394	0.412
$\phi p1$	1.40	1.50	1.60	0.055	0.059	0.063	K1	0.75	0.8	0.85	0.030	0.031	0.033
$\phi p2$	1.15	1.20	1.25	0.045	0.047	0.049							

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